



UTRON

UT62W256C

Rev. 1.1

32K X 8 BIT LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	Draft Date
Rev. 1.0	Original.	Aug.13. 2001
Rev. 1.1	1.Add Extended temperature : -20 ~85 2.Add order information for lead free product	Apr. 21. 2003



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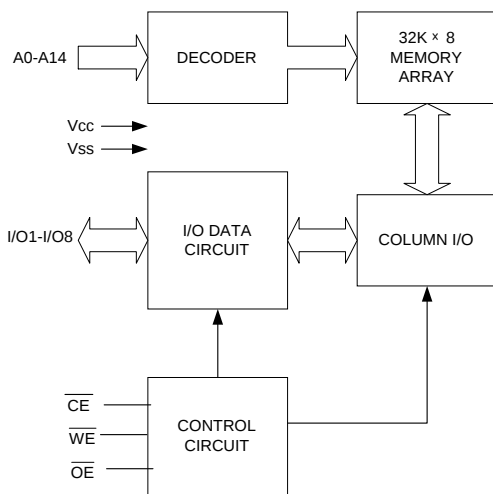
UT62W256C

32K X 8 BIT LOW POWER CMOS SRAM

FEATURES

- Fast access time : 35/70ns
- Low power consumption:
 - Operation : 40/20 mA (max.) (V_{CC} 3.6V)
 - 50/40 mA (max.) (V_{CC} 5.5V)
 - Standby : -L / -LL version
 - 1 / 0.5uA (typical) $V_{CC}=2.7\sim3.6V$
 - 2 / 1uA (typical) $V_{CC}=4.5\sim5.5V$
- Wide Range power supply: 2.7V~5.5V
- Operating temperature :
 - Commercial temperature : 0 ~70
 - Extended temperature : -20 ~85
- All inputs and outputs are TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 1.5V (min.)
- Package : 28-pin 600 mil PDIP
- 28-pin 330 mil SOP
- 28-pin 8x13.4mm STSOP

FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A14	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
V_{CC}	Power Supply
V_{SS}	Ground

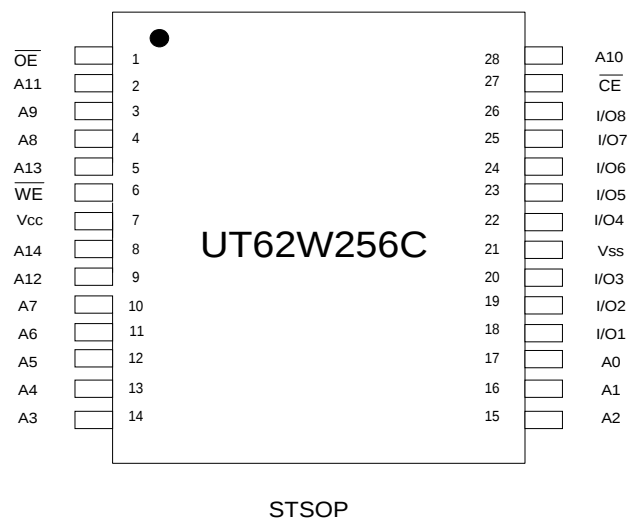
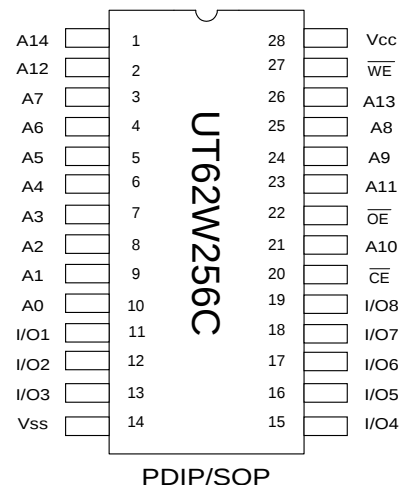
GENERAL DESCRIPTION

The UT62W256C is a 262,144-bit low power CMOS static random access memory organized as 32,768 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology. its standby current is stable within the range of operating temperature.

The UT62W256C is designed for low power application. It is particularly well suited for battery back-up nonvolatile memory application.

The UT62W256C operates with wide range power supply and all inputs and outputs are fully TTL compatible

PIN CONFIGURATION





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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V_{SS}	V_{TERM}	-0.5 to 7.0	V
Operation Temperature	Commercial	T_A	0 to 70
	Extended	T_A	-20 to 85
Storage Temperature	T_{STG}	-65 to 150	
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA
Soldering Temperature (under 10 sec)	T_{solder}	260	

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High - Z	I_{SB}, I_{SB1}
Output Disable	L	H	H	High - Z	I_{CC}, I_{CC1}, I_{CC2}
Read	L	L	H	D_{OUT}	I_{CC}, I_{CC1}, I_{CC2}
Write	L	X	L	D_{IN}	I_{CC}, I_{CC1}, I_{CC2}

Note: H = V_{IH} , L = V_{IL} , X = Don't care.

DC ELECTRICAL CHARACTERISTICS ($T_A = 0$ to 70 / -20 to 85 (E))

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNIT
Power Supply Voltage	V_{CC}		2.7~3.6			4.5~5.5			V
Input High Voltage	V_{IH}^{*1}		2.0	-	$V_{CC}+0.5$	2.2	-	$V_{CC}+0.5$	V
Input Low Voltage	V_{IL}^{*2}		-0.5	-	0.6	-0.5	-	0.8	V
Input Leakage Current	I_{LI}	$V_{SS} \quad V_{IN} \quad V_{CC}$	-1	-	1	-1	-	1	μA
Output Leakage Current	I_{LO}	$V_{SS} \quad V_{I/O} \quad V_{CC},$ $\overline{CE} = V_{IH} \text{ or } \overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$	-1	-	1	-1	-	1	μA
Output High Voltage	V_{OH}	$I_{OH} = -1mA$	2.2	-	-	2.4	-	-	V
Output Low Voltage	V_{OL}	$I_{OL} = 4mA$	-	-	0.4	-	-	0.4	V
Operation Power Supply Current	I_{CC}	$\overline{CE} = V_{IL}, I_{I/O} = 0mA, \text{Cycle} = \text{Min.}$	-35	-	40	-	40	50	mA
			-70	-	20	-	30	40	mA
	I_{CC1}	Cycle=1 μs $\overline{CE} = 0.2V$; $I_{I/O} = 0mA$ other pins at 0.2V or $V_{CC}-0.2V$	-	-	6	-	-	10	mA
	I_{CC2}	Cycle=500ns $\overline{CE} = 0.2V$; $I_{I/O} = 0mA$ other pins at 0.2V or $V_{CC}-0.2V$	-	-	12	-	-	20	mA
Standby Power Supply Current	I_{SB}	$\overline{CE} = V_{IH}$	-	-	3	-	-	3	mA
	I_{SB1}	$\overline{CE} \quad V_{CC}-0.2V$	-L	-	1	-	2	100	μA
			-LL	-	0.5	-	1	50	μA

Notes:

1. Overshoot : $V_{CC}+2.0v$ for pulse width less than 10ns.
2. Undershoot : $V_{SS}-2.0v$ for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.

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PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C_{IN}	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 100\text{Pf} + 1\text{TTL}$, $I_{OH}/I_{OL} = -1\text{mA}/4\text{mA}$

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.7\text{V} \sim 5.5\text{V}$, $T_A = 0^\circ\text{C}$ to 70°C / -20°C to 85°C (E))**(1) READ CYCLE**

PARAMETER	SYMBOL	UT62W256C-35		UT62W256C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	35	-	70	-	ns
Address Access Time	t_{AA}	-	35	-	70	ns
Chip Enable Access Time	t_{ACE}	-	35	-	70	ns
Output Enable Access Time	t_{OE}	-	25	-	35	ns
Chip Enable to Output in Low Z	t_{CLZ^*}	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ^*}	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ^*}	-	25	-	35	ns
Output Disable to Output in High Z	t_{OHZ^*}	-	25	-	35	ns
Output Hold from Address Change	t_{OH}	5	-	5	-	ns

(2) WRITE CYCLE

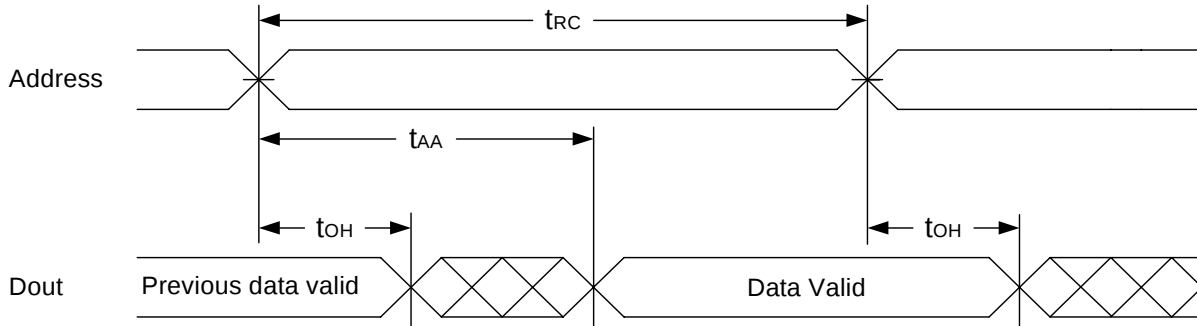
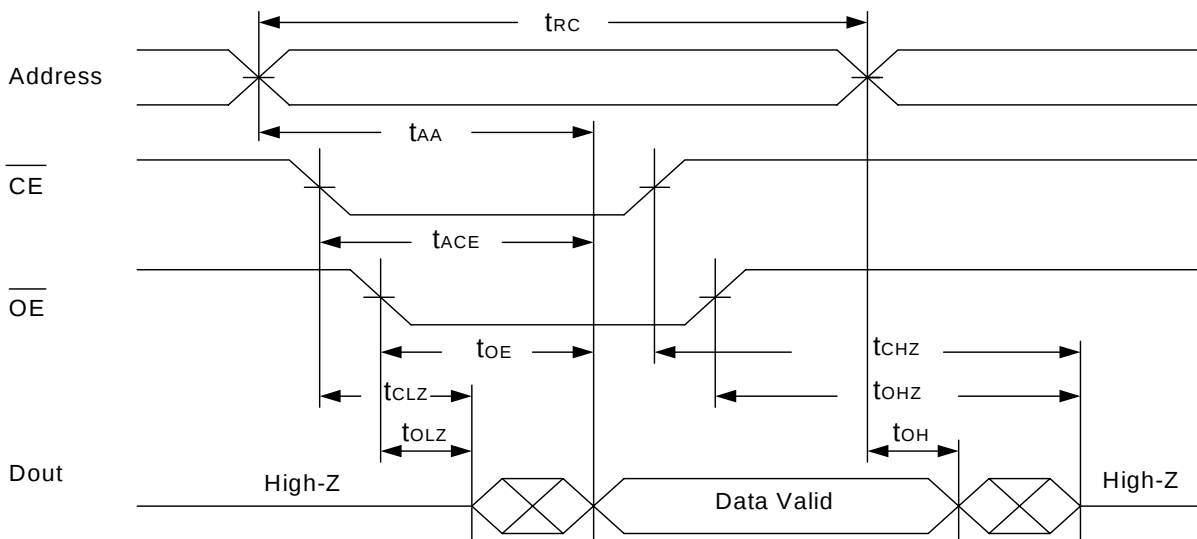
PARAMETER	SYMBOL	UT62W256C-35		UT62W256C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	35	-	70	-	ns
Address Valid to End of Write	t_{AW}	30	-	60	-	ns
Chip Enable to End of Write	t_{CW}	30	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	ns
Write Pulse Width	t_{WP}	25	-	50	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	20	-	30	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	ns
Output Active from End of Write	t_{OW^*}	5	-	5	-	ns
Write to Output in High Z	t_{WHZ^*}	-	15	-	25	ns

*These parameters are guaranteed by device characterization, but not production tested.



TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)

READ CYCLE 2 ($\overline{CE}$ and $\overline{OE}$ Controlled) (1,3,4,5)

Notes :

1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected $\overline{OE}$ = low, $\overline{CE}$ = low.
3. Address must be valid prior to or coincident with $\overline{CE}$ = low.; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{OLZ} , t_{CHZ} and t_{OHZ} are specified with C_L = 5pF. Transition is measured ± 500 mV from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ} .



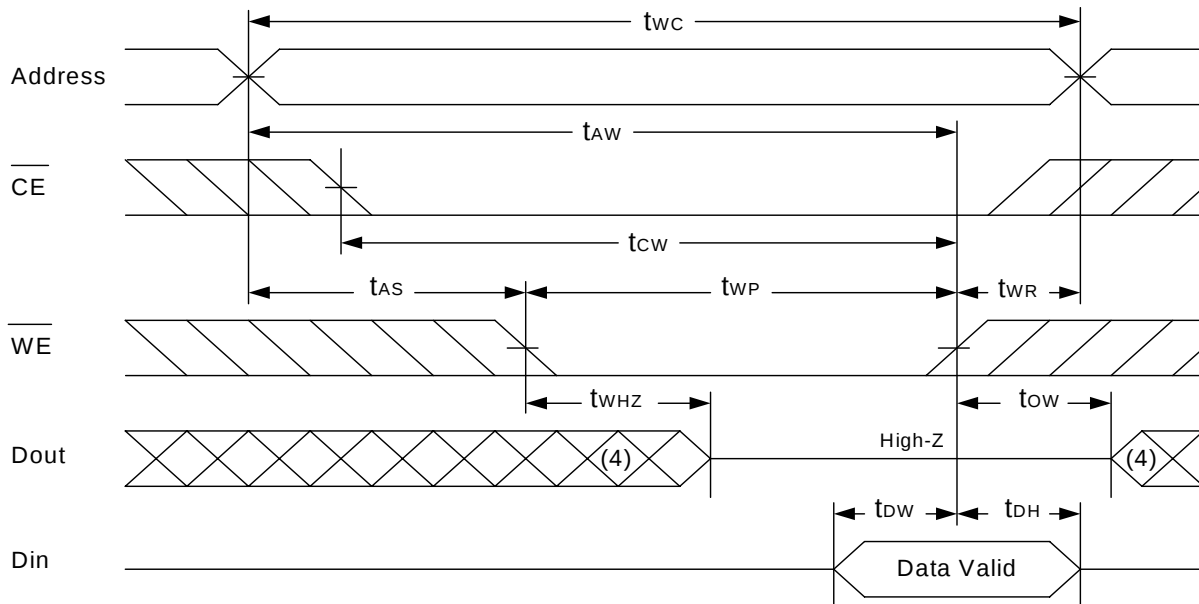
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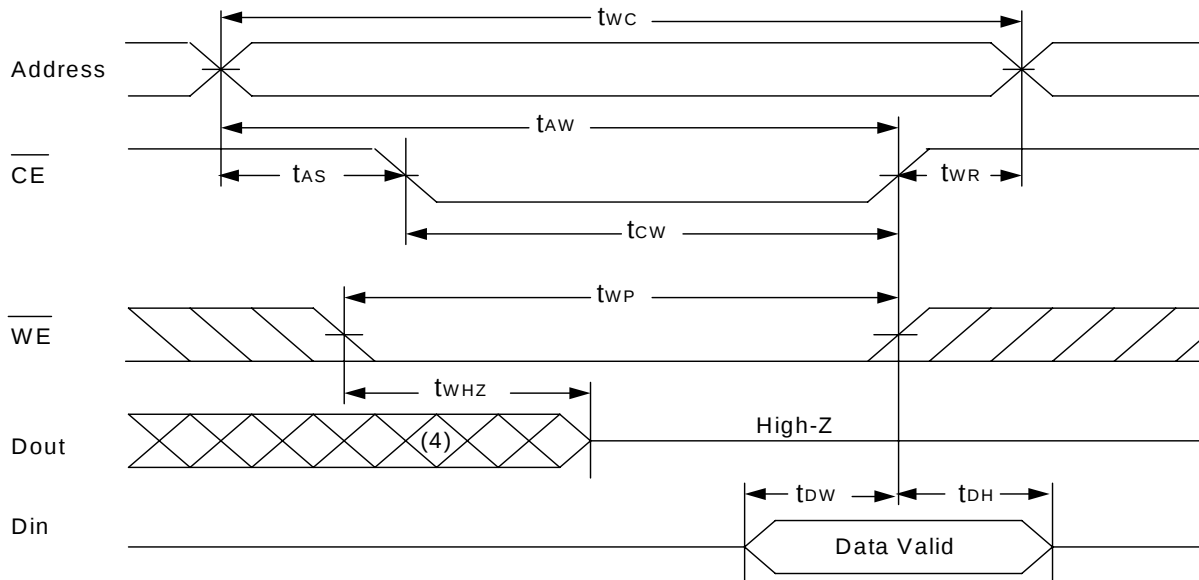
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WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ($\overline{CE}$ Controlled) (1,2,5,6)





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Notes :

1. $\overline{WE}$, $\overline{CE}$ must be high during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE}$, low $\overline{WE}$.
3. During a $\overline{WE}$ controlled write cycle with $\overline{OE}$ low, t_{WP} must be greater than $t_{WHZ} + t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$ low transition occurs simultaneously with or after $\overline{WE}$ low transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.

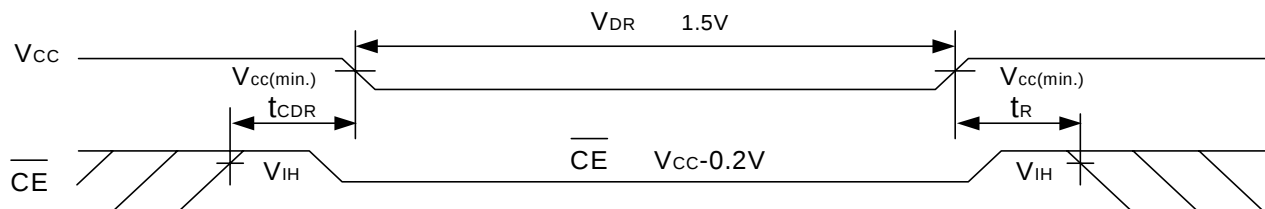
DATA RETENTION CHARACTERISTICS ($T_A = 0$ to 70 / -20 to 85 (E))

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	$\overline{CE}$ $V_{CC}-0.2V$	1.5	-	5.5	V
Data Retention Current	I_{DR}	$V_{CC}=1.5V$ $\overline{CE}$ $V_{CC}-0.2V$	- L	1	20	μA
			- LL	0.5	10	μA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t_R		t_{RC*}	-	-	ns

t_{RC*} = Read Cycle Time

DATA RETENTION WAVEFORM

Low Vcc Data Retention Waveform ($\overline{CE}$ controlled)





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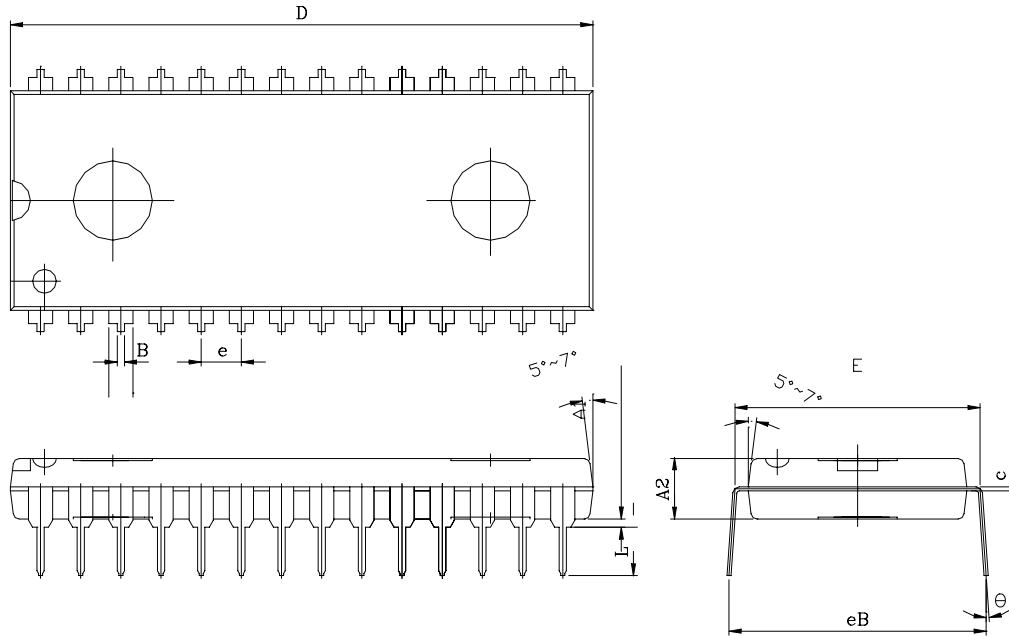
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PACKAGE OUTLINE DIMENSION

28 pin 600 mil PDIP PACKAGE OUTLINE DIMENSION



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A1	0.010(MIN)	0.254(MIN)
A2	0.150±0.001	3.810±0.254
B	0.018±0.005	0.457±0.127
c	0.010±0.004	0.254±0.102
D	1.460±0.005	37.084±0.127
E	0.600±0.010	15.240±0.254
e	0.100 (TYP)	2.540(TYP)
eB	0.640±0.03	16.256±0.762
L	0.130±0.010	3.302±0.254
θ	0°~15°	0°~15°



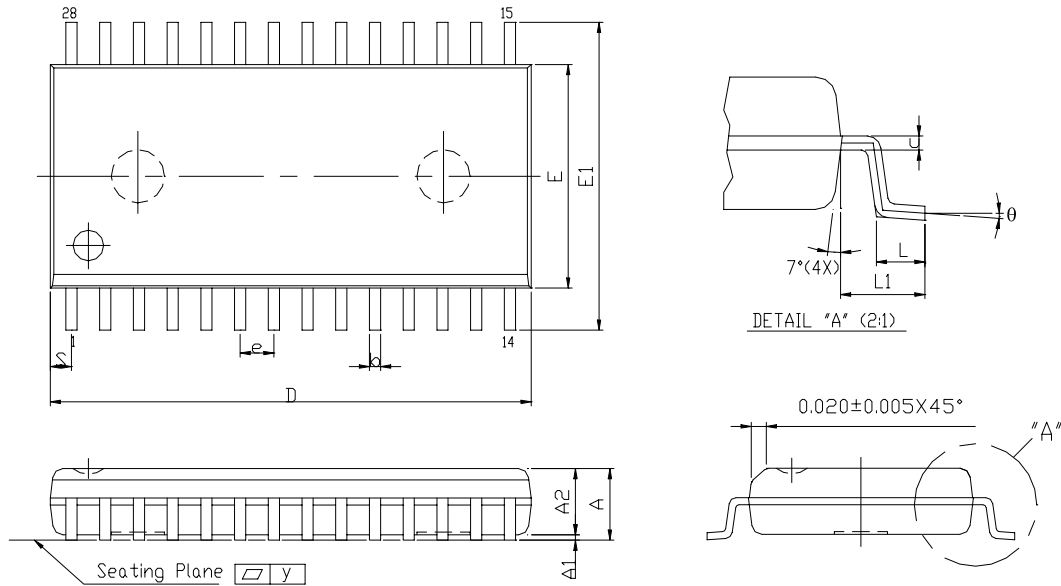
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28 pin 330 mil SOP PACKAGE OUTLINE DIMENSION



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A	0.112 (MAX)	2.845 (MAX)
A1	0.004(MIN)	0.102(MIN)
A2	0.098±0.005	2.489±0.127
b	0.016 (TYP)	0.406(TYP)
c	0.010 (TYP)	0.254(TYP)
D	0.713±0.005	18.110±0.127
E	0.331±0.005	8.407±0.127
E1	0.465±0.012	11.811±0.305
e	0.050 (TYP)	1.270(TYP)
L	0.0404±0.008	1.0255±0.203
L1	0.067±0.008	1.702 ±0.203
S	0.047 (MAX)	1.194 (MAX)
y	0.003(MAX)	0.076(MAX)
θ	0° 10°	0° 10°



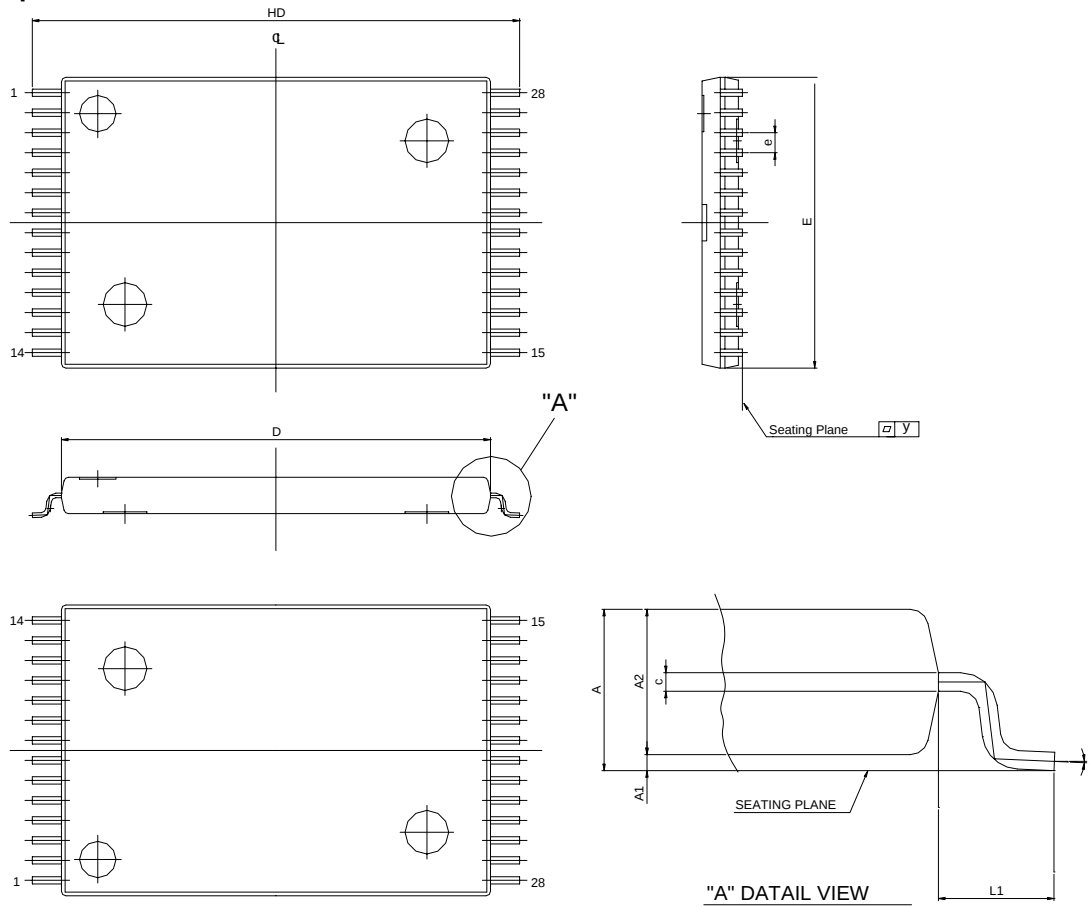
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28 pin 8x13.4mm STSOP PACKAGE OUTLINE DIMENSION



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A	0.047 (MAX)	1.20 (MAX)
A1	0.004 ±0.002	0.10 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
D	0.465 ±0.004	11.800 ±0.100
E	0.315 ±0.004	8.000 ±0.100
e	0.022 (TYP)	0.55 (TYP)
HD	0.528 ±0.008	13.40 ±0.20.
L1	0.0315 ±0.004	0.80 ±0.10
y	0.003 (MAX)	0.076 (MAX)
Θ	0° 5°	0° 5°



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ORDERING INFORMATION

Commercial temperature :

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) max.	PACKAGE
UT62W256CPC-35L	35	100 μ A	28PIN PDIP
UT62W256CPC-35LL	35	50 μ A	28PIN PDIP
UT62W256CPC-70L	70	100 μ A	28PIN PDIP
UT62W256CPC-70LL	70	50 μ A	28PIN PDIP
UT62W256CSC-35L	35	100 μ A	28PIN SOP
UT62W256CSC-35LL	35	50 μ A	28PIN SOP
UT62W256CSC-70L	70	100 μ A	28PIN SOP
UT62W256CSC-70LL	70	50 μ A	28PIN SOP
UT62W256CLS-35L	35	100 μ A	28PIN STSOP
UT62W256CLS-35LL	35	50 μ A	28PIN STSOP
UT62W256CLS-70L	70	100 μ A	28PIN STSOP
UT62W256CLS-70LL	70	50 μ A	28PIN STSOP

Extended temperature :

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) max.	PACKAGE
UT62W256CPC-35LE	35	100 μ A	28PIN PDIP
UT62W256CPC-35LLE	35	50 μ A	28PIN PDIP
UT62W256CPC-70LE	70	100 μ A	28PIN PDIP
UT62W256CPC-70LLE	70	50 μ A	28PIN PDIP
UT62W256CSC-35LE	35	100 μ A	28PIN SOP
UT62W256CSC-35LLE	35	50 μ A	28PIN SOP
UT62W256CSC-70LE	70	100 μ A	28PIN SOP
UT62W256CSC-70LLE	70	50 μ A	28PIN SOP
UT62W256CLS-35LE	35	100 μ A	28PIN STSOP
UT62W256CLS-35LLE	35	50 μ A	28PIN STSOP
UT62W256CLS-70LE	70	100 μ A	28PIN STSOP
UT62W256CLS-70LLE	70	50 μ A	28PIN STSOP

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32K X 8 BIT LOW POWER CMOS SRAM**ORDERING INFORMATION (for lead free product)**

Commercial temperature :

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) max.	PACKAGE
UT62W256CPCL-35L	35	100 μ A	28PIN PDIP
UT62W256CPCL-35LL	35	50 μ A	28PIN PDIP
UT62W256CPCL-70L	70	100 μ A	28PIN PDIP
UT62W256CPCL-70LL	70	50 μ A	28PIN PDIP
UT62W256CSCL-35L	35	100 μ A	28PIN SOP
UT62W256CSCL-35LL	35	50 μ A	28PIN SOP
UT62W256CSCL-70L	70	100 μ A	28PIN SOP
UT62W256CSCL-70LL	70	50 μ A	28PIN SOP
UT62W256CLSL-35L	35	100 μ A	28PIN STSOP
UT62W256CLSL-35LL	35	50 μ A	28PIN STSOP
UT62W256CLSL-70L	70	100 μ A	28PIN STSOP
UT62W256CLSL-70LL	70	50 μ A	28PIN STSOP

Extended temperature :

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) max.	PACKAGE
UT62W256CPCL-35LE	35	100 μ A	28PIN PDIP
UT62W256CPCL-35LLE	35	50 μ A	28PIN PDIP
UT62W256CPCL-70LE	70	100 μ A	28PIN PDIP
UT62W256CPCL-70LLE	70	50 μ A	28PIN PDIP
UT62W256CSCL-35LE	35	100 μ A	28PIN SOP
UT62W256CSCL-35LLE	35	50 μ A	28PIN SOP
UT62W256CSCL-70LE	70	100 μ A	28PIN SOP
UT62W256CSCL-70LLE	70	50 μ A	28PIN SOP
UT62W256CLSL-35LE	35	100 μ A	28PIN STSOP
UT62W256CLSL-35LLE	35	50 μ A	28PIN STSOP
UT62W256CLSL-70LE	70	100 μ A	28PIN STSOP
UT62W256CLSL-70LLE	70	50 μ A	28PIN STSOP



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